

### **REMARKS**

Claim 10 has been amended, and claims 9, 11, 24 and 26 have been canceled. Accordingly, claims 10 and 25 are still active in this application. The amendment to claim 10 further clarifies the fact that the regions adjacent the source and drain regions are those regions which controls current flow.

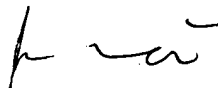
Claim 10 was rejected under 35 U.S.C. 102(b) as being anticipated by Jones (U.S. 4,212,683). The rejection is respectfully traversed.

Claim 10 requires, among other features, a channel region between the source/drain regions in the substrate having a relatively low  $V_T$  central region between the source/drain regions and relatively high controlling  $V_T$  regions adjacent to the source/drain regions, the channel region having an implanted one of a positive or negative  $V_T$  dopant intermediate the source/drain regions and having an implanted one of a negative or positive  $V_T$  dopant adjacent the source/drain regions, the opposite of the dopant in the central region as discussed above. This claim refers to the fourth embodiment as discussed on pages 5 and 9 of the specification. No such features are taught or suggested by Sasaki either alone or in the total combination as claimed. The term “controlling  $V_T$ ” is defined at page 3, lines 10ff as that region which is the least conducting region and thus controls the current flow. Nothing in Jones et al. defines the regions 28, 29 as performing that function and no reason is stated in Jones et al. why those regions should perform the function as now claimed. This feature more clearly defines the invention over the prior art.

Claim 25 depends from claim 10 and therefore defines patentably over Sasaki for at least the reasons set forth as to claim 10.

In view of the above remarks, favorable reconsideration and allowance are respectfully requested.

Respectfully submitted,

A handwritten signature in cursive script, appearing to read "J. Cantor".

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